

What is claimed is:

1. A capacitor used in an RF circuit, comprising an upper electrode, a lower electrode, and a dielectric layer interposed between the upper electrode and the lower electrode,
wherein a plurality of electrodes are formed in parallel in the dielectric layer in a diagonal direction, first electrodes, which are half of the plurality of electrodes, are coupled to only the upper electrode, and second electrodes, which are the other half of the plurality of electrodes, are coupled to only the lower electrode, and the first electrodes and the second electrodes are alternately positioned in rows and columns.
2. The capacitor as claimed in claim 1, wherein at least one of the first electrodes and at least one of the second electrodes are positioned in a staircase form and comprise a plurality of conductive plugs and a plurality of metal layers for coupling the conductive plugs in parallel,
wherein the conductive plugs are horizontally spaced apart from each other by an interval that is smaller than the horizontal length of the metal layers and vertically spaced apart from each other by an interval that is equal to the thickness of the metal layers.
3. The capacitor as claimed in claim 2, wherein at least one of the first electrodes and at least one of the second electrodes comprise:
two conductive plugs, which are horizontally spaced apart from each other by an interval that is smaller than the length of the metal layers and vertically spaced apart from each other by an interval that is equal to the thickness of the metal layers, and
one metal layer, which couples a lower end of one of the two conductive plugs to an upper end of the other conductive plug.
4. The capacitor as claimed in claim 1, wherein the dielectric layer is a Si_3N_4 layer.